

PATENT ASSIGNMENT COVER SHEET

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SUBMISSION TYPE:	NEW ASSIGNMENT	
NATURE OF CONVEYANCE:	ASSIGNMENT	
CONVEYING PARTY DATA		
	Name	Execution Date
	AISAWA TECHNOLOGIES, LLC	11/26/2019
RECEIVING PARTY DATA		
Name:	INTELLECTUAL VENTURES ASSETS 158 LLC	
Street Address:	251 LITTLE FALLS DRIVE	
City:	WILMINGTON	
State/Country:	DELAWARE	
Postal Code:	19808	
PROPERTY NUMBERS Total: 14		
Property Type	Number	
Patent Number:	5753552	
Patent Number:	5998255	
Patent Number:	6069037	
Patent Number:	6110835	
Patent Number:	6114200	
Patent Number:	6140201	
Patent Number:	6153465	
Patent Number:	6156664	
Patent Number:	6169016	
Patent Number:	6200848	
Patent Number:	6291295	
Patent Number:	6313006	
Patent Number:	6337240	
Patent Number:	6403411	
CORRESPONDENCE DATA		
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NAME OF SUBMITTER:	LAWRENCE A. AARONSON
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SIGNATURE:	/Lawrence A. Aaronson/
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DATE SIGNED:	01/28/2020
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Total Attachments: 8

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ASSIGNMENT OF RIGHTS IN CERTAIN ASSETS

For good and valuable consideration, the receipt of which is hereby acknowledged, Aisawa Technologies, LLC, a Delaware limited liability company, having an address at 251 Little Falls Drive, Wilmington, DE 19808 ("Assignor"), does hereby sell, assign, transfer, and convey unto Intellectual Ventures Assets 158 LLC, a Delaware limited liability company, having an address at 251 Little Falls Drive, Wilmington, DE 19808 ("Assignee"), or its designees, the right, title, and interest in and to any and all of the following provisional patent applications, patent applications, patents, and other governmental grants or issuances of any kind (the "Certain Assets"):

<u>Patent or Application No.</u>	<u>Country</u>	<u>Grant Date Filing Date</u>	<u>Title of Patent and First Named Inventor</u>
5753552 (08/790793)	US	5/19/1998 (1/30/1997)	Method For Fabricating A Storage Electrode Without Polysilicon Bridge And Undercut Sheng, Yi-Chung
TWI118174 (TW087109134)	TW	7/21/2000 (6/9/1998)	The Manufacturing Method Of DRAM Capacitor Kung, Cheng-Chih
5998255 (09/145711)	US	12/7/1999 (9/2/1998)	Method Of Fabricating DRAM Capacitor Kung, Cheng-Chih
TWI129634 (TW087113976)	TW	4/1/2001 (8/25/1998)	Manufacturing Method For Embedded DRAM Liao, Kuan-Yang
6069037 (09/191677)	US	5/30/2000 (11/13/1998)	Method Of Manufacturing Embedded DRAM Liao, Kuan-Yang
6110835 (09/164620)	US	8/29/2000 (10/1/1998)	Method For Fabricating An Electrode Structure For A Cylindrical Capacitor In Integrated Circuit Wang, Chuan-Fu
TWI108165 (TW087106845)	TW	10/21/1999 (5/4/1998)	Manufacturing Method For Cylinder Capacitor Wang, Chuan-Fu
6114200 (08/996697)	US	9/5/2000 (12/23/1997)	Method Of Fabricating A Dynamic Random Access Memory Device Yew, Tri-Rung
(DE19801854.1)	DE	(1/20/1998)	DRAM Production Process Yew, Tri-Rung

<u>Patent or Application No.</u>	<u>Country</u>	<u>Grant Date Filing Date</u>	<u>Title of Patent and First Named Inventor</u>
JP2944603 (JP10-009448)	JP	6/25/1999 (1/21/1998)	Manufacture Of Dynamic Random Access Memory Device Yew, Tri-Rung
FR2765397 (FR9800712)	FR	6/8/2001 (1/23/1998)	DRAM Production Process Yew, Tri-Rung
TWI105953 (TW086109104)	TW	8/11/1999 (6/28/1997)	Manufacturing Method Of DRAM Yew, Tri-Rung
TWI120616 (TW087112947)	TW	9/21/2000 (8/6/1998)	Manufacture Of The Cylinder-Type Capacitor Of DRAM Jeng, J. S. Jason
6140201 (09/172407)	US	10/31/2000 (10/14/1998)	Method For Fabricating A Cylinder Capacitor Jeng, J. S. Jason
TWI112085 (TW086118028)	TW	2/21/2000 (12/1/1997)	Method For Fabricating DRAM Capacitor Jeng, Jason
6153465 (09/008863)	US	11/28/2000 (1/20/1998)	Method Of Fabricating A Capacitor Of Dynamic Random Access Memory Jeng, Jason
TWI148012 (TW088100963)	TW	1/1/2002 (1/22/1999)	Contact Isolation Structure And The Manufacturing Method Thereof Gau, Jing-Hong
6156664 (09/267883)	US	12/5/2000 (3/11/1999)	Method Of Manufacturing Liner Insulating Layer Gau, Jing-Hong
6169016 (09/181302)	US	1/2/2001 (10/28/1998)	Method Of Forming Contact Chien, Sun-Chieh
6200848 (09/208612)	US	3/13/2001 (12/8/1998)	Method Of Fabricating Self-Aligned Contact In Embedded DRAM Lin, Yung-Chang

<u>Patent or Application No.</u>	<u>Country</u>	<u>Grant Date Filing Date</u>	<u>Title of Patent and First Named Inventor</u>
TWI117046 (TW087113405)	TW	7/1/2000 (8/14/1998)	A Manufacturing Method Of Self-Alignment Contact, SAC, In Embedded DRAM Lin, Yung-Chang
6291295 (09/316979)	US	9/18/2001 (5/24/1999)	Method Of Forming A Storage Electrode Of A Capacitor On An Ion-Implanted Isolation Layer Huang, Kuo-Tai
TWI149572 (TW088106507)	TW	1/21/2002 (4/23/1999)	Manufacturing Method Of The Storage Electrode Of DRAM Capacitor Huang, Kuo-Tai
6313006 (09/048637)	US	11/6/2001 (3/26/1998)	Method Of Field Implantation Hsue, C. C.
TWI109661 (TW087100223)	TW	12/1/1999 (1/9/1998)	Method Of Field Implantation Hsue, C. C.
TWI122207 (TW087117426)	TW	10/21/2000 (10/21/1998)	Manufacture Method For Embedded DRAM Chu, Chih-Hsun
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6403411 (09/208601)	US	6/11/2002 (12/8/1998)	Method For Manufacturing Lower Electrode Of DRAM Capacitor Chu, Chih-Hsun
(JP11-008158)	JP	(1/14/1999)	Manufacture Of Lower Electrode In DRAM Capacitor Chu, Chih-Hsun

Assignor assigns to Assignee all rights to the inventions, invention disclosures, and discoveries in the assets listed above, together, with the rights, if any, to revive prosecution of claims under such assets and to sue or otherwise enforce any claims under such assets for past, present or future infringement.

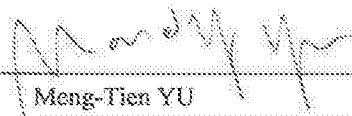
Assignor hereby authorizes the respective patent office or governmental agency in each jurisdiction to make available to Assignee all records regarding the Certain Assets.

The terms and conditions of this Assignment of Rights in Certain Assets will inure to the benefit of Assignee, its successors, assigns, and other legal representatives and will be binding upon Assignor, its successors, assigns, and other legal representatives.

DATED this 26th day of November, 2019.

ASSIGNOR:

Aisawa Technologies, LLC

By: 
Name: Meng-Tien YU
Title: Authorized Person

ASSIGNEE:

Intellectual Ventures Assets 158 LLC

By: _____
Name: Lawrence Froeber
Title: Chief Financial Officer

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Aisawa Technologies, LLC

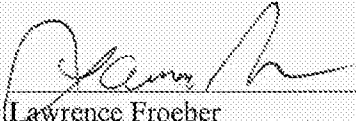
By: _____

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Title: _____

ASSIGNEE:

Intellectual Ventures Assets 158 LLC

By:  _____

Name: Lawrence Froeber

Title: Chief Financial Officer